

Diffusion bonding of tungsten / EUROFER97 using vanadium interlayer

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IMF III FUTURE MATERIALS PROCESSING II

Activity 1: Fabrication Process Development
Task: Development of diffusion bonded tungsten / EUROFER97 joints
WP: WP10-MAT-WWALLOY-01-09KIT/BS
Reporting Period: February 2010 - June 2010
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Institution: KIT

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Diffusion bonding of tungsten to EUROFER97

→ Large differences in the coefficient of thermal expansion (CTE) between tungsten and steel

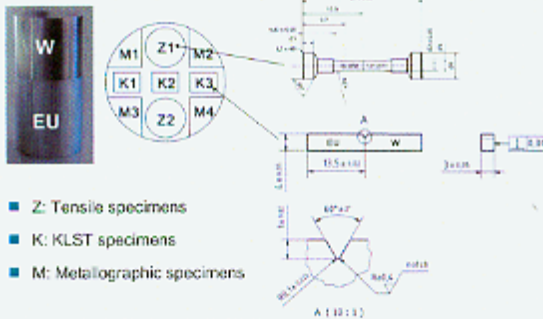
CTE of tungsten at 20 °C: $4.5 \times 10^{-6} \text{ K}^{-1}$
 CTE of steel at 20 °C: $12.0 \times 10^{-6} \text{ K}^{-1}$

Diffusion bonding process:

- Uniaxial diffusion bonding
- Surface roughness of tungsten and EUROFER97, $R_z < 1 \mu\text{m}$
- Bonding at 1050 °C
- Bonding duration up to 9 h
- Bonding pressure is calculated using the creep parameter of EUROFER97 for a secondary creep, ϵ_s of about 8 %

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Specimens after diffusion bonding

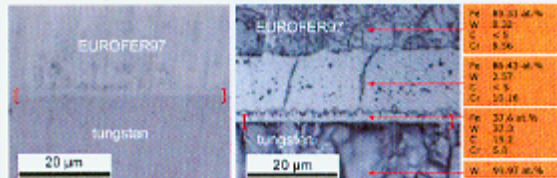


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Microstructure at bonding seam of diffusion bonded specimen - without post bonding heat treatment

Bonding temperature at 1050 °C
 Bonding duration: 4 h

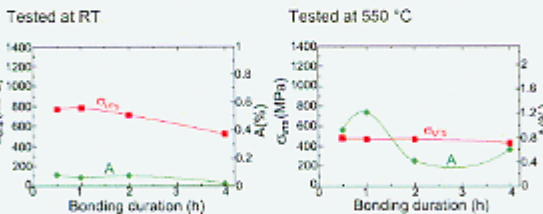
before etching



- Sound joining
- Intermetallic phases at the interface

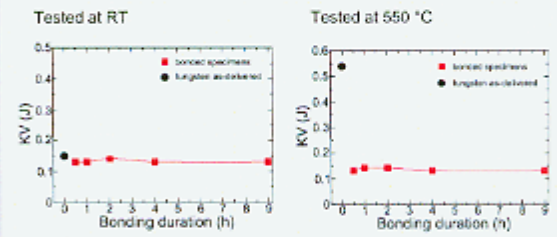
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Tensile tests on diffusion bonded specimens - without post bonding heat treatment



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Charpy impact tests on diffusion bonded specimens - without post bonding heat treatment



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Diffusion bonding of tungsten to EUROFER97 using 1 mm thick vanadium interlayer

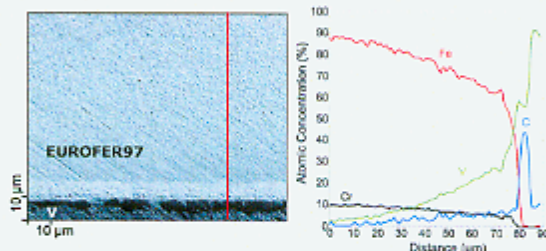


→ Coefficient of thermal expansion of vanadium at 20 °C: $8.5 \times 10^{-6} \text{ K}^{-1}$

Diffusion bonding process:

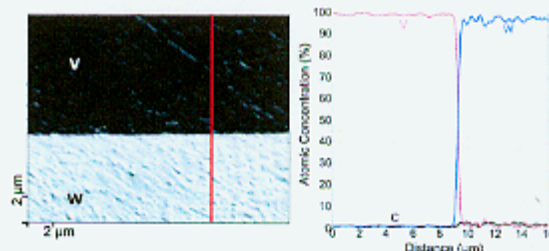
- Uniaxial diffusion bonding
- Surface roughness of vanadium plate, R_a : 711 – 1282 nm
- Bonding at 1050 °C and 1 h
- Bonding pressure of 19 MPa calculated using the creep parameter of EUROFER97 for a secondary creep, $\dot{\epsilon}_s$ of about 8 %
- Post bonding annealing at 760 °C and 90 min

Interface between EUROFER97 and vanadium interlayer



- Sound bonding interface
- Layers consist of intermetallic phases and vanadium carbide

Interface between vanadium and tungsten interlayer

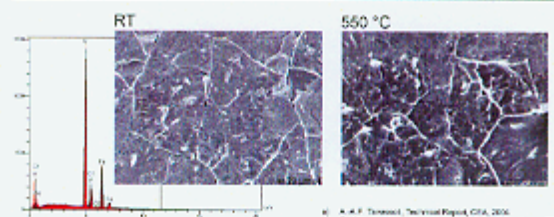


- Sound bonding interface
- No layer with intermetallic phases at the interface

Mechanical Properties and fracture surfaces



	RT			550 °C		
	joint	W	EUROFER	joint	W	EUROFER
σ_{UTS} (MPa)	207	1280	516 ^{#1}	172	430	335 ^{#1}
KV (J)	0.14	0.15	9.63 ^{#1}	0.17	0.61	



#1: A. F. Townsend, Technical Report, CEA, 2004
#2: M. L. Williams et al., Mater. Sci. Eng., 2007

Summary & Outlook



Performed Work (February 2010 - June 2010)

- Diffusion bonding of W to EUROFER97 using V as interlayer at 1050 °C
- investigation of the mechanical properties of the bonded specimens by tensile tests, and Charpy impact test at RT and 550 °C.
- investigation of the microstructure of the bonded specimens at the bonding seam by AES
- Fracture analysis of the broken tensile specimens by EDX

Work planned for the next period

- Continuation of the diffusion bonding experiments and their characterization using V as interlayer at various bonding temperatures lower than 1050 °C
- Varying the bonding duration at the optimized bonding temperature.

Work planned for WP 2011

- Diffusion bonding of tungsten / EUROFER97 using Nb as interlayer